Paper List

January—December, 2025

E2025-1(F) Metal Contamination Behavior on Silicon Dioxide Surface Rinsed With Deionized Water Containing Ultra-Trace Metal During Single-Wafer Cleaning
IEEE Transactions on Semiconductor Manufacturing, Vol.38, No.3, (2025), pp.492-498
K. Tsutano, T. Mawaki, Y. Shirai, R. Kuroda
DOI: 10.1109/TSM.2025.3575743

E2025-2(C) On the determination threshold of illumination-adaptive signal selection technology for multi-stage LOFIC CMOS image sensors
2025 International Image Sensor Workshop (IISW2025), pp.61-64, R02.5, June 2, (2025), Hyogo
Yoshihito Hirai, Kohei Takizawa, Takezo Mawaki, Rihito Kuroda
DOI: https://doi.org/10.60928/wjde-as5j

E2025-3(C) Statistical Capacitance Measurement of Si Trench Capacitors Using Array Test Circuit
Extended Abstracts of the 2025 International Conference on Solid State Devices and Materials (SSDM2025), pp.165-166, C-1-03, September 16, (2025), Yokohama
Ryoya Nishimaki, Koga Saito, Takezo Mawaki, Ken Miyauchi, Rihito Kuroda

E2025-4(C) [Invited]
Progress in Development of Advanced High Dynamic Range CMOS Image Sensors
PROCEEDINGS OF THE INTERNATIONAL DISPLAY WORKSHOPS, VOL. 32, 2025 (IDW '25), pp. 1612-1615 (IST1-1) December 4, Hiroshima
Ken Miyauchi
https://pub-files.atlas.jp/fs/public/idw2025/ver_14/abstract/en/IST1-01.pdf

E2025-5(C) A 120 dB Dynamic Range 3D Stacked 2-Stage LOFIC CMOS Image Sensor with Illuminance-Adaptive Signal Selection Function
71st Annual IEEE International Electron Devices Meeting (IEDM2025), 42-2, December 10, (2025), San Francisco, US
Kohei Takizawa, Yoshihito Hirai, Masaya Yoshida, Takezo Mawaki, Ken Miyauchi, Rihito Kuroda

E2025-6(C) A Global Shutter Burst CMOS Image Sensor with 6-Tpixel/s Readout Speed, 256-recording Frames and -170dB Parasitic Light Sensitivity

71st Annual IEEE International Electron Devices Meeting(IEDM2025), 42-5, December 10, (2025), San Francisco, US

Masuto Kitamura, Yasunori Kawaguchi, Naoya Kuriyama, Tomoaki Maeda, Toshifumi Imamura, Takezo Mawaki, Shigetoshi Sugawa, Rihito Kuroda